

# **CSD17318Q2 30V N-Channel NexFET™ Power MOSFET**

### 1 Features

- Optimized for 5V gate drive
- Low capacitance and charge
- Low R<sub>DS(ON)</sub>
- Low-thermal resistance
- Lead free
- RoHS compliant
- Halogen free
- SON 2mm × 2mm plastic package

# 2 Applications

- Storage, tablets, and handheld devices
- Optimized for load switch applications
- DC-DC converters
- Battery and load management applications

# 3 Description

This 30V, 12.6mΩ, 2mm × 2mm SON NexFET™ power MOSFET is designed to minimize losses in power conversion applications and optimized for 5V gate drive applications. The 2mm × 2mm SON offers excellent thermal performance for the size of the package.

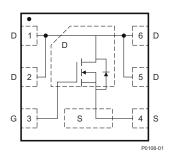
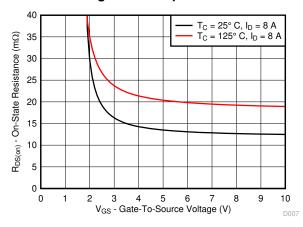


Figure 3-1. Top View



On-State Resistance vs Gate to Source Voltage

### **Product Summary**

T <sub>A</sub> = 25°	C	TYPICAL VA	UNIT		
V <sub>DS</sub>	Drain-to-Source Voltage	30		V	
Qg	Gate Charge Total (4.5V)	6.0		nC	
Q <sub>gd</sub>	Gate Charge Gate-to-Drain	1.3	nC		
		V <sub>GS</sub> = 2.5V 20			
R <sub>DS(on)</sub>	Drain-to-Source On-Resistance	V <sub>GS</sub> = 4.5V	13.9	mΩ	
		V <sub>GS</sub> = 8V 12.6			
V <sub>GS(th)</sub>	Threshold Voltage	0.9		V	

### **Device Information** (1)

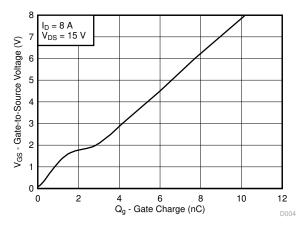
PART NUMBER	QTY	MEDIA	PACKAGE	SHIP
CSD17318Q2	3000		SON	Таре
CSD17318Q2T	250	7 Inch Reel	2.00mm × 2.00mm Plastic Package	and Reel

For all available packages, see the orderable addendum at the end of the data sheet.

### **Absolute Maximum Ratings**

T <sub>A</sub> = 2	5°C	VALUE	UNIT	
V <sub>DS</sub>	Drain-to-Source Voltage	30	٧	
V <sub>GS</sub>	Gate-to-Source Voltage	±10	٧	
	Continuous Drain Current (Package Limited)	21.5		
I <sub>D</sub>	Continuous Drain Current (Silicon Limited), T <sub>C</sub> = 25°C	25	Α	
	Continuous Drain Current <sup>(1)</sup>	10		
I <sub>DM</sub>	Pulsed Drain Current, T <sub>A</sub> = 25°C <sup>(2)</sup>	68	Α	
D	Power Dissipation <sup>(1)</sup>	2.5	W	
P <sub>D</sub>	Power Dissipation, T <sub>C</sub> = 25°C	16		
T <sub>J</sub> , T <sub>STG</sub>	Operating Junction, Storage Temperature	-55 to 150	°C	
E <sub>AS</sub>	Avalanche Energy, Single Pulse, $I_D$ = 12.4A, L = 0.1mH, $R_G$ = 25 $\Omega$	7.7	mJ	

- Typical  $R_{\theta JA} = 55^{\circ} \text{C/W}$  on a  $1\text{in}^2$ , 2oz Cu pad on a (1) 0.06in thick FR4 PCB.
- Max  $R_{\theta JC}$  = 7°C/W, pulse duration ≤ 100µs, duty cycle ≤ 1%. (2)



**Gate Charge** 



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# **4 Specifications**

# **4.1 Electrical Characteristics**

 $T_A = 25$ °C (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
STATIC	CHARACTERISTICS		•			
BV <sub>DSS</sub>	Drain-to-source voltage	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	30			V
I <sub>DSS</sub>	Drain-to-source leakage	V <sub>GS</sub> = 0V, V <sub>DS</sub> = 24V			1	μΑ
I <sub>GSS</sub>	Gate-to-source leakage	V <sub>DS</sub> = 0V, V <sub>GS</sub> = 10V			100	nA
V <sub>GS(th)</sub>	Gate-to-source threshold voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	0.6	0.9	1.2	V
		V <sub>GS</sub> = 2.5V, I <sub>D</sub> = 8A		20	30	
R <sub>DS(on)</sub>	Drain-to-source on-resistance	$V_{GS} = 4.5V, I_D = 8A$		13.9	16.9	mΩ
		V <sub>GS</sub> = 8V, I <sub>D</sub> = 8A		12.6	15.1	
g <sub>fs</sub>	Transconductance	V <sub>DS</sub> = 3V, I <sub>D</sub> = 8A		42		S
DYNAM	IC CHARACTERISTICS		-			
C <sub>iss</sub>	Input capacitance			676	879	pF
C <sub>oss</sub>	Output capacitance	$V_{GS} = 0V, V_{DS} = 15V,$ f = 1MHz		71	92	pF
C <sub>rss</sub>	Reverse transfer capacitance	<i>j</i> = 10012		39	51	pF
$R_G$	Series gate resistance			1.0	2.0	Ω
Qg	Gate charge total (4.5 V)			6.0		nC
Q <sub>gd</sub>	Gate charge gate-to-drain	V <sub>DS</sub> = 15V, I <sub>D</sub> = 8A		1.3		nC
Q <sub>gs</sub>	Gate charge gate-to-source			1.5		nC
Q <sub>g(th)</sub>	Gate charge at Vth			0.7		nC
Q <sub>oss</sub>	Output charge	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V		2.7		nC
t <sub>d(on)</sub>	Turnon delay time			5		ns
t <sub>r</sub>	Rise time	V <sub>DS</sub> = 15V, V <sub>GS</sub> = 4.5V,		16		ns
t <sub>d(off)</sub>	Turnoff delay time	$I_D = 8A, R_G = 2\Omega$		13		ns
t <sub>f</sub>	Fall time			4		ns
DIODE (	CHARACTERISTICS	•	1			
V <sub>SD</sub>	Diode forward voltage	I <sub>SD</sub> = 8A, V <sub>GS</sub> = 0V		0.8	1.0	V
Q <sub>rr</sub>	Reverse recovery charge	V <sub>DD</sub> = 15V, I <sub>F</sub> = 8A,		2.9		nC
t <sub>rr</sub>	Reverse recovery time	di/dt = 300A/µs		12		ns

# 4.2 Thermal Characteristics

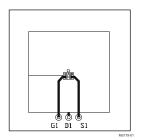
T<sub>A</sub> = 25°C (unless otherwise noted)

	PARAMETER	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	R <sub>0JC</sub> Thermal resistance junction-to-case <sup>(1)</sup>				°C/W
$R_{\theta JA}$	Thermal resistance junction-to-ambient <sup>(1)</sup> (2)			65	°C/W

<sup>(1)</sup> R<sub>0JC</sub> is determined with the device mounted on a 1in<sup>2</sup> (6.45cm<sup>2</sup>), 2oz (0.071mm) thick Cu pad on a 1.5in × 1.5in (3.81cm × 3.81cm), 0.06in (1.52mm) thick FR4 PCB. R<sub>0JC</sub> is specified by design, whereas R<sub>0JA</sub> is determined by the user's board design.

<sup>(2)</sup> Device mounted on FR4 material with 1in<sup>2</sup> (6.45cm<sup>2</sup>), 2oz (0.071mm) thick Cu.





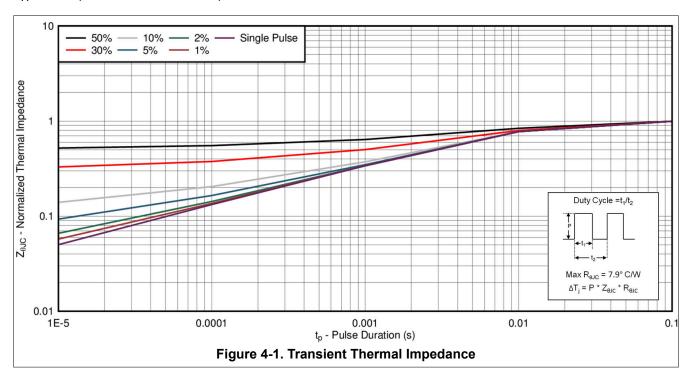
Max  $R_{\theta JA} = 65^{\circ}C/W$  when mounted on 1in<sup>2</sup> (6.45cm<sup>2</sup>) of 2oz (0.071mm) thick Cu.

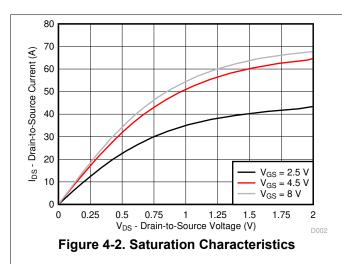


Max  $R_{\theta JA}$  = 250°C/W when mounted on a minimum pad area of 2oz (0.071mm) thick

# 4.3 Typical MOSFET Characteristics

T<sub>A</sub> = 25°C (unless otherwise noted)





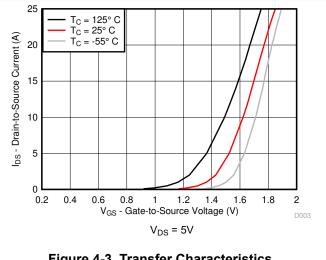
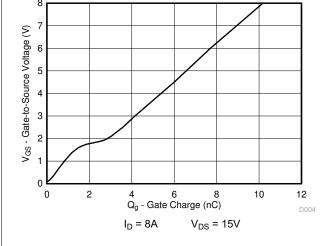


Figure 4-3. Transfer Characteristics

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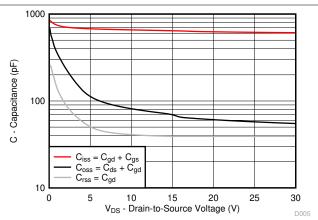
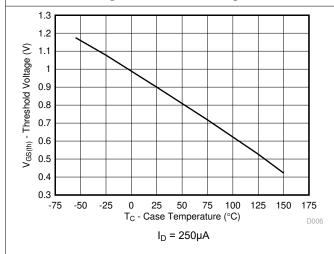


Figure 4-5. Capacitance





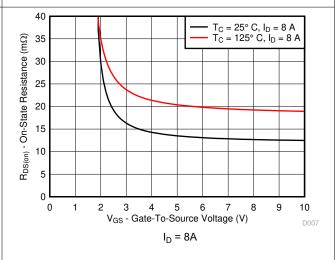
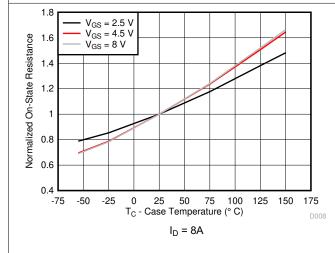
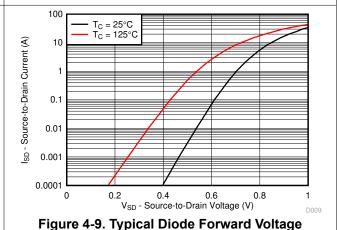


Figure 4-6. Threshold Voltage vs Temperature







riguic + o. Typical Blode i orward voltage

Figure 4-8. Normalized On-State Resistance vs
Temperature

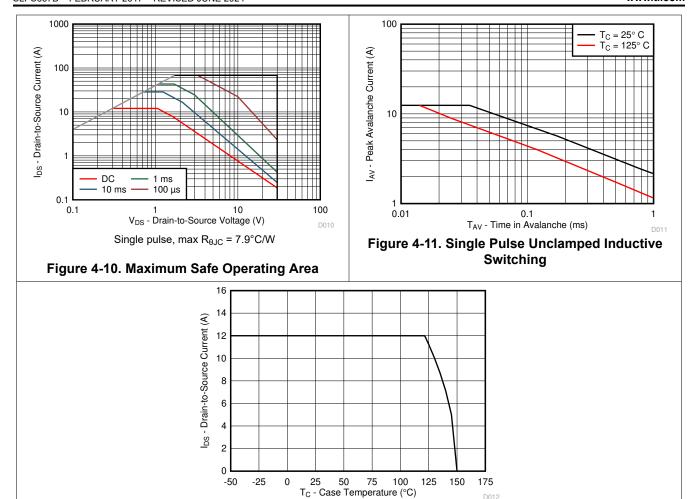


Figure 4-12. Maximum Drain Current vs Temperature

# 5 Device and Documentation Support

# 5.1 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

# **5.2 Support Resources**

TI E2E™ support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

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### 5.3 Trademarks

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# **6 Revision History**

### Changes from Revision A (February 2017) to Revision B (June 2024)

**Page** 

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# 7 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

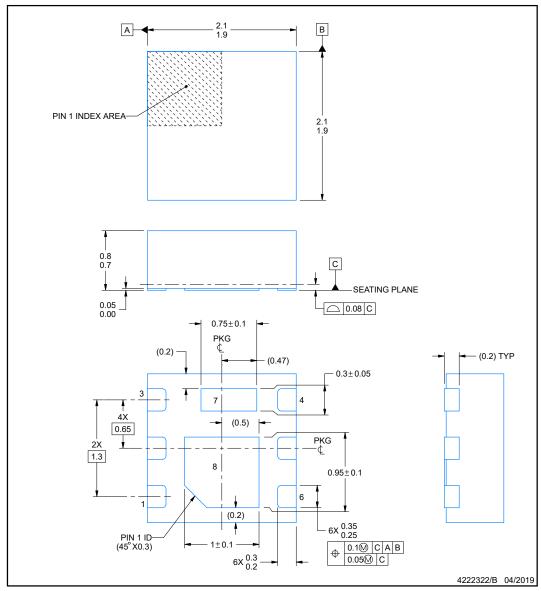
### 7.1 Mechanical Data

**DQK0006C** 

## **PACKAGE OUTLINE**

### WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



### NOTES:

- All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
   This drawing is subject to change without notice.
   The package thermal pads must be soldered to the printed circuit board for thermal and mechanical performance.



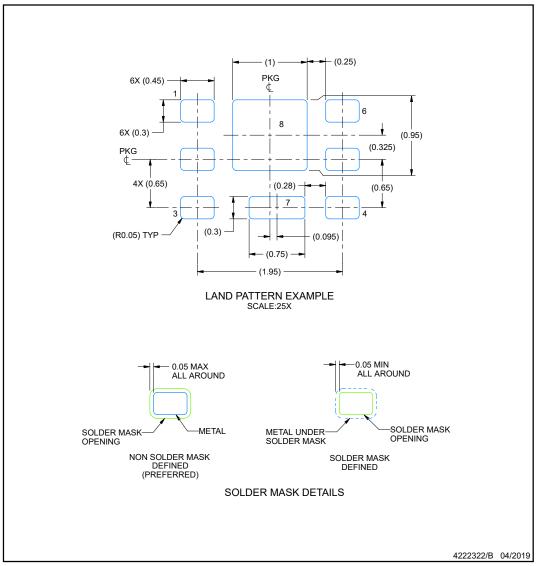


## **EXAMPLE BOARD LAYOUT**

# **DQK0006C**

### WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).



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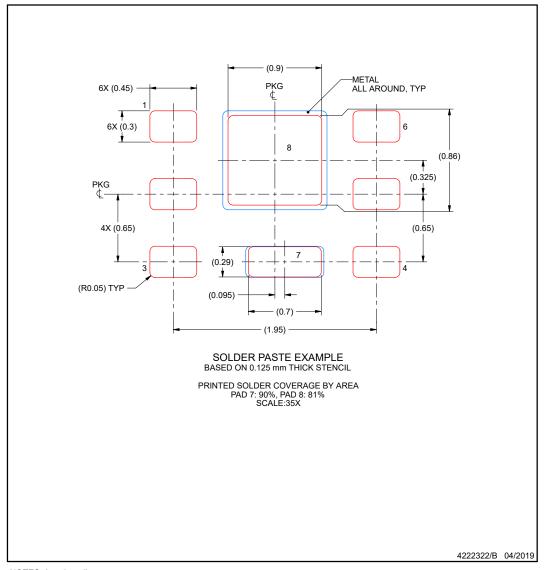
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## **EXAMPLE STENCIL DESIGN**

# **DQK0006C**

### WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



NOTES: (continued)

5. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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### PACKAGING INFORMATION

Orderable part number	Status	Material type	Package   Pins	Package qty   Carrier	RoHS	Lead finish/	MSL rating/	Op temp (°C)	Part marking
	(1)	(2)			(3)	Ball material	Peak reflow		(6)
						(4)	(5)		
CSD17318Q2	Active	Production	WSON (DQK)   6	3000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-55 to 150	1718
CSD17318Q2.B	Active	Production	WSON (DQK)   6	3000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-55 to 150	1718
CSD17318Q2G4.B	Active	Production	WSON (DQK)   6	3000   LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-55 to 150	1718
CSD17318Q2T	Active	Production	WSON (DQK)   6	250   SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-55 to 150	1718
CSD17318Q2T.B	Active	Production	WSON (DQK)   6	250   SMALL T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-55 to 150	1718

<sup>(1)</sup> Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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<sup>(5)</sup> MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

<sup>(6)</sup> Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

# **PACKAGE MATERIALS INFORMATION**

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## TAPE AND REEL INFORMATION





A0	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



### \*All dimensions are nominal

Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD173180	Q2 WSON	DQK	6	3000	180.0	9.5	2.3	2.3	1.0	4.0	8.0	Q1
CSD17318C	2T WSON	DQK	6	250	180.0	9.5	2.3	2.3	1.0	4.0	8.0	Q1

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### \*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CSD17318Q2	WSON	DQK	6	3000	189.0	185.0	36.0
CSD17318Q2T	WSON	DQK	6	250	189.0	185.0	36.0

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